

2SK3777-01R

N-CHANNEL SILICON POWER MOSFET

FUJI
ELECTRIC

■ Outline Drawings (mm) 200406

FUJI POWER MOSFET Super FAP-G Series

■ Features

High speed switching Low on-resistance
No secondary breakdown Low driving power
Avalanche-proof

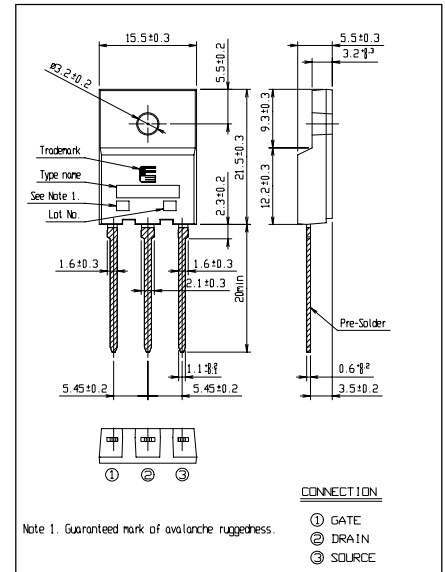
■ Applications

Switching regulators DC-DC converters
UPS (Uninterruptible Power Supply)

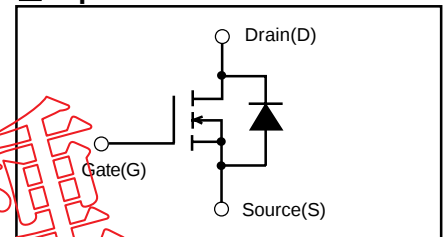
■ Maximum ratings and characteristic

● Absolute maximum ratings (T_c=25°C unless otherwise specified)

Item	Symbol	Ratings	Unit	Remarks
Drain-source voltage	V _{DS}	300	V	
	V _{DSX}	300	V	V _{GS} =-30V
Continuous Drain Current	I _D	53	A	
Pulsed Drain Current	I _D (puls)	±212	A	
Gate-Source Voltage	V _{GS}	±30	V	
Maximum Avalanche current	I _{AR}	53	A	Note *1
Non-Repetitive	E _{AS}	1013.9	mJ	Note *2
Maximum Avalanche Energy	E _{AR}	41	mJ	Note *3
Repetitive	dV _{DS} /dt	20	kV/μs	V _{DS} ≤300V
Maximum Drain-Source dV/dt	dV/dt	5	kV/μs	Note *4
Peak Diode Recovery dV/dt	P _D	210	W	T _c =25°C
Max. Power Dissipation	T _{ch}	+150	°C	T _a =25°C
Operating and Storage Temperature range	T _{stg}	-55 to +150	°C	



■ Equivalent circuit schematic



Note *1: T_{ch}≤150°C, Repetitive and Non-repetitive

Note *2: Starting T_{ch}=25°C, I_{AS}=22A, L=3.03mH,

V_{GS}=48V, R_G=50Ω

E_{AS} limited by maximum channel temperature and Avalanche current.

See to the 'Avalanche Energy' graph

Note *3: Repetitive rating: Pulse width limited by maximum channel temperature.

See to the 'Transient Thermal impedance' graph.

Note *4: I_{AS}≤-I_D, -di/dt=50A/μs, V_{CC}≤BV_{DSS}, T_{ch}≤150°C

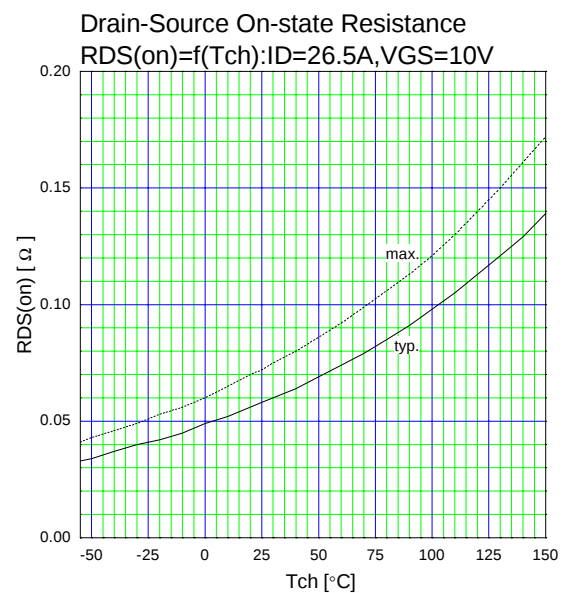
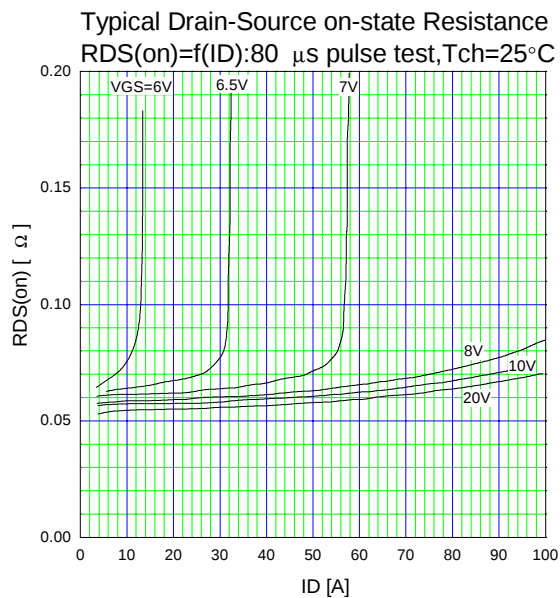
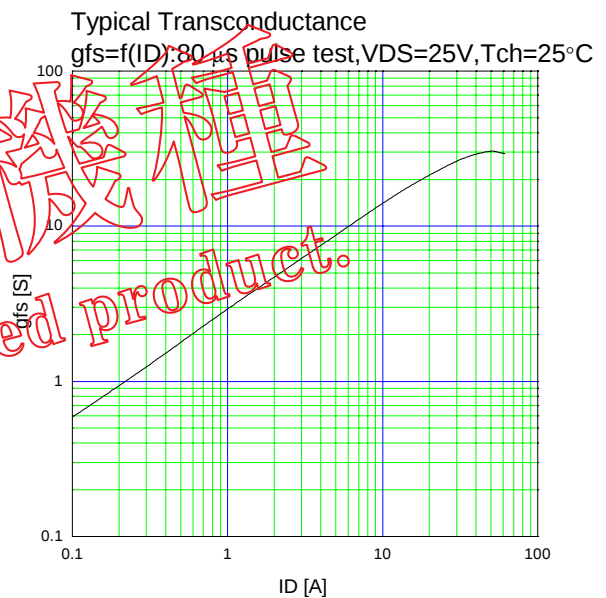
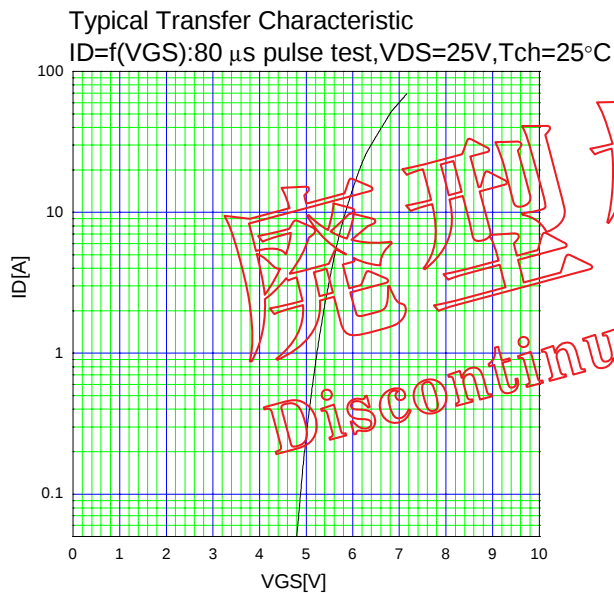
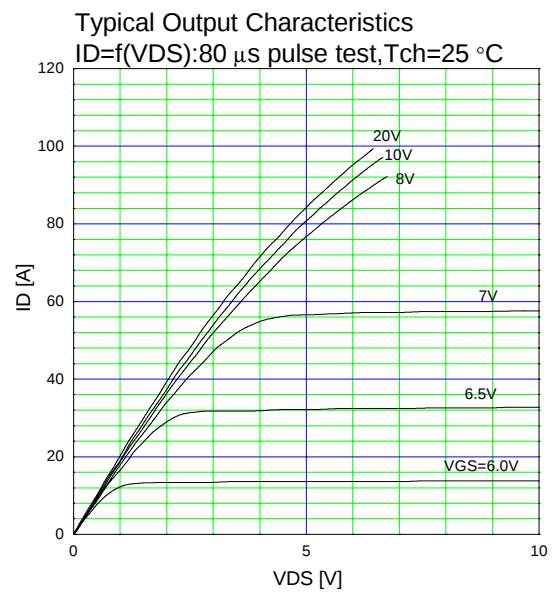
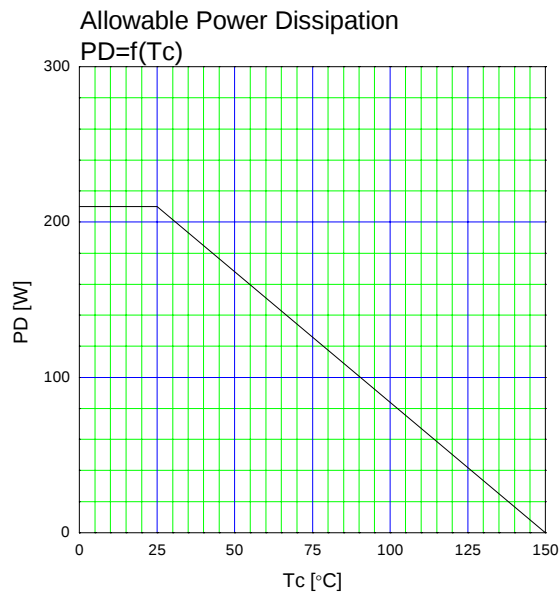
● Electrical characteristics (T_c=25°C unless otherwise specified)

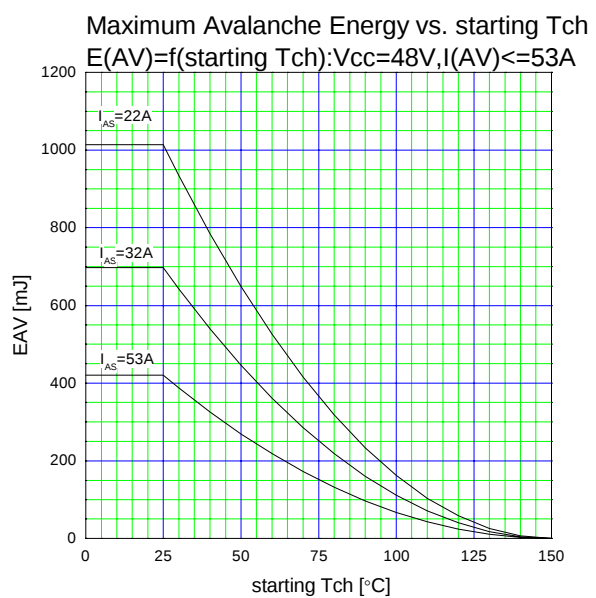
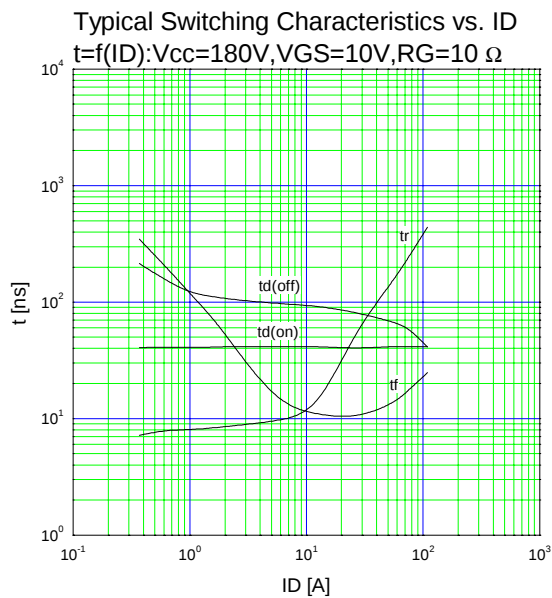
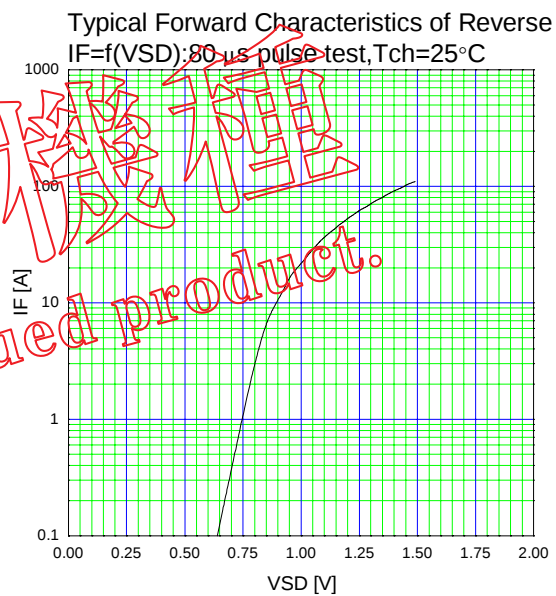
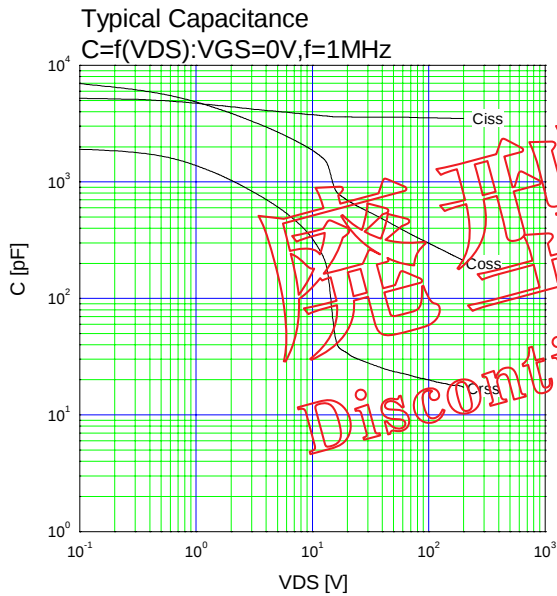
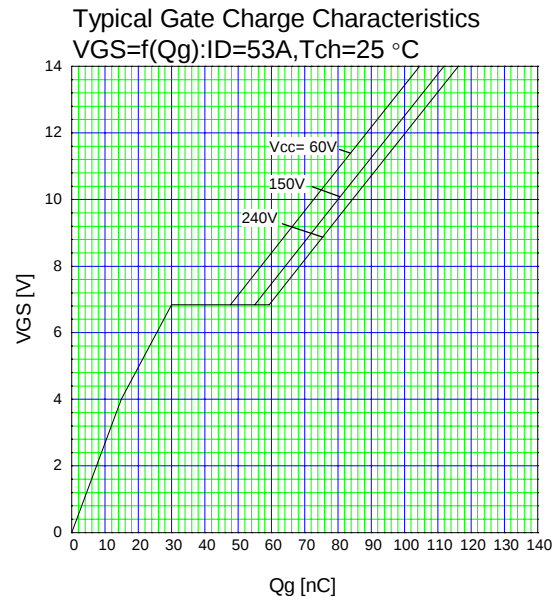
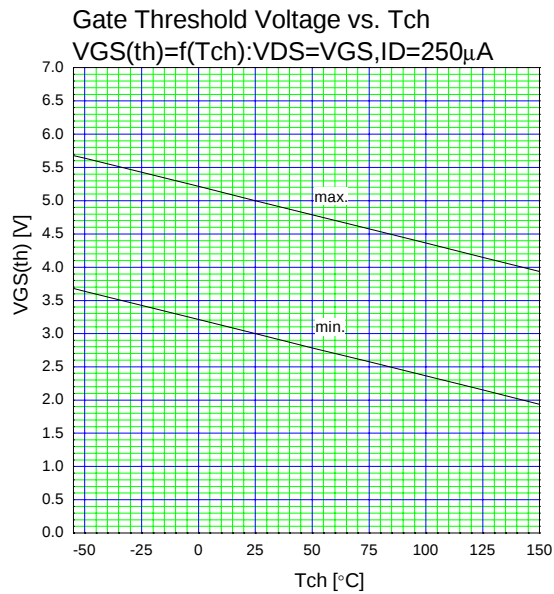
Item	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Drain-Source Breakdown Voltage	BV _{DSS}	I _D =250μA V _{GS} =0V	300			V
Gate Threshold Voltage	V _{GS(th)}	I _D =250μA V _{DS} =V _{GS}	3.0		5.0	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =300V V _{GS} =0V V _{DS} =240V V _{GS} =0V			25 250	μA
Gate-Source Leakage Current	I _{GSS}	V _{GS} =±30V V _{DS} =0V			100	nA
Drain-Source On-State Resistance	R _{DS(on)}	I _D =26.5A V _{GS} =10V		58	72	mΩ
Forward Transconductance	g _{fs}	I _D =26.5A V _{DS} =25V	12	24		S
Input Capacitance	C _{iss}	V _{DS} =25V		3600	5475	pF
Output Capacitance	C _{oss}	V _{GS} =0V		610	915	
Reverse Transfer Capacitance	C _{rss}	f=1MHz		30	45	
Turn-On Time t _{on}	t _{d(on)} t _r	V _{CC} =180V I _D =26.5A		40 58	60 87	ns
Turn-Off Time t _{off}	t _{d(off)} t _f	V _{GS} =10V R _{GS} =10Ω		82 10	123 15	
Total Gate Charge	Q _G	V _{CC} =150V		80	120	nC
Gate-Source Charge	Q _{GS}	I _D =53A		30	45	
Gate-Drain Charge	Q _{GD}	V _{GS} =10V		25	38	
Diode forward on-voltage	V _{SD}	I _F =53A V _{GS} =0V T _{ch} =25°C		1.20	1.50	V
Reverse recovery time	t _{rr}	I _F =53A V _{GS} =0V		420		ns
Reverse recovery charge	Q _{rr}	-di/dt=100A/μs T _{ch} =25°C		5.0		μC

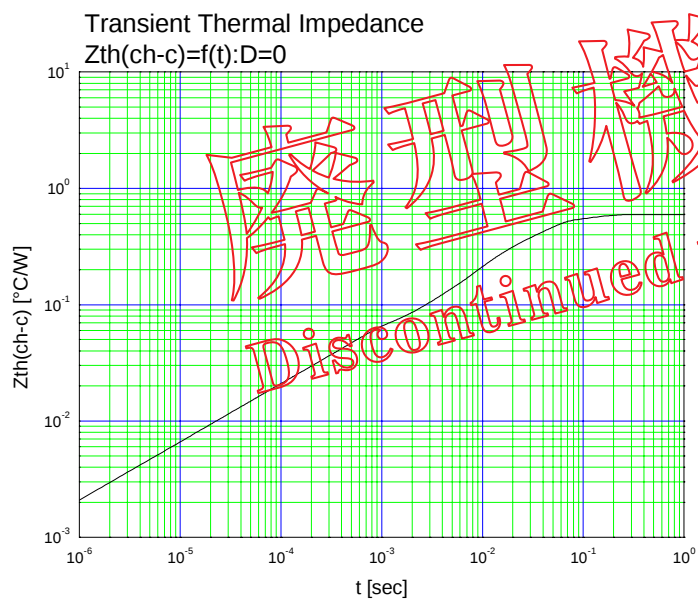
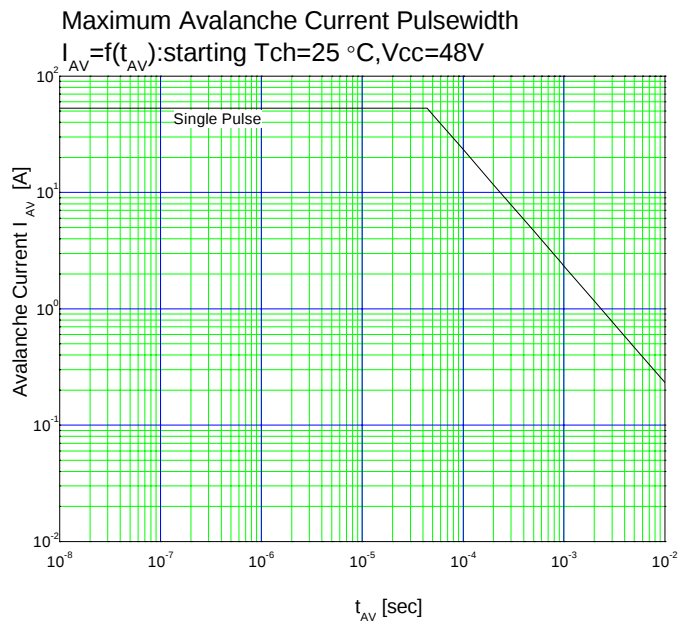
● Thermal characteristics

Item	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Thermal resistance	R _{th(ch-c)} R _{th(ch-a)}	channel to case channel to ambient			0.595 40.0	°C/W

Characteristics







廢型機種
Discontinued product.